



Ruttonsha International Rectifier Ltd.

SILICON RECTIFIERS

TYPE : R3200Q.. CF SERIES

FAST RECOVERY DIODES

Features

- High power FAST recovery diode series
- 7.0 μ s recovery time
- High voltage ratings up to 4500V
- High current capability
- Optimized turn on and turn off characteristics
- Low forward recovery
- Fast and soft reverse recovery
- Press-puk encapsulation
- Maximum junction temperature 150°C

Hockey Puk Version

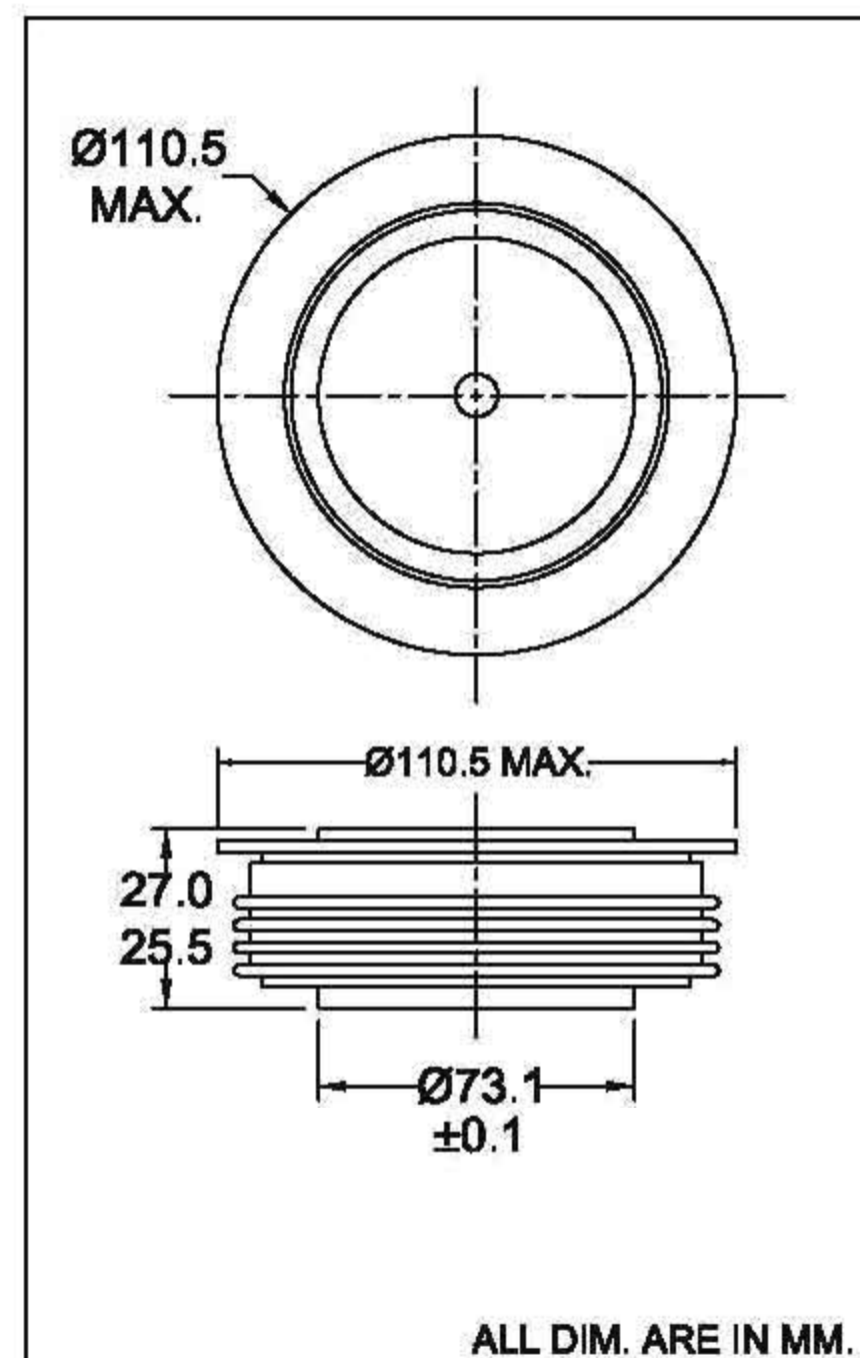
3200A

Typical Applications

- Snubber diode for GTO
- High voltage free-wheeling diode
- Fast recovery rectifier applications

Major Ratings and Characteristics

Parameters	R3200Q	Units
$I_{F(AV)}$	3230	A
@ T_{hs}	55	°C
$I_{F(RMS)}$	5080	A
I_{FSM} @ 50Hz	20	KA
V_{RRM} range	3000 to 4500	V
t_{rr}	7.0	μ s
@ T_J	150	°C
T_J	-40 to 150	°C



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ELECTRICAL SPECIFICATIONS

Voltage Ratings

Type number	Voltage Code	V_{RRM} , maximum repetitive peak reverse voltage V	V_{RSM} , maximum non-repetitive peak rev. voltage V	I_{RRM} max. @ $T_J = T_J$ max. mA
R3200Q...CF	30	3000	3100	150
	34	3400	3500	
	38	3800	3900	
	42	4200	4300	
	45	4500	4600	

Forward Conduction

Parameter	R3200Q...CF	Units	Conditions
$I_{F(AV)}$ Max. average forward current @ heatsink temperature	3230	A	180° conduction, half sine wave
	55	°C	Double side cooled
$I_{F(RMS)}$ Max. RMS forward current	5080	A	@ 55°C heatsink temperature double side cooled
I_{FSM} Max. peak, one-cycle forward, non-repetitive surge current	20	KA	t = 10ms Sinusoidal half wave, Initial $T_J = T_J$ max.
I^2t Maximum I^2t for fusing	2000	KA ² s	t = 10ms
$V_{F(TO)}$ Threshold voltage	1.25	V	$T_J = T_J$ max.
r_f Forward slope resistance	0.15	mΩ	$T_J = T_J$ max.
V_{FM} Max. forward voltage drop	2.0	V	$I_{pk} = 3000A$, $T_c = 25^\circ C$, $t_p = 10ms$ sinusoidal wave
t_{rr} Reverse Recovery Time	7.0	us	IFM=1000A, di/dt=100A/us

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Thermal and Mechanical Specifications

Parameter	R3200Q...CF	Units	Conditions
T _J Max. junction operating temperature range	-40 to 150	°C	
T _{stg} Max. storage temperature range	-40 to 150		
R _{thJ-hs} Max. thermal resistance, junction to heatsink	0.012	K/W	DC operation double side cooled
F Mounting force, ± 10%	40	KN (Kg)	
wt Approximate weight	1050	g	
Case style	Q - PUK		See Outline Table

Ordering Information Table

Device Code													
	<table border="1" style="margin-left: auto; margin-right: auto;"> <tr> <td style="padding: 5px;">R</td> <td style="padding: 5px;">3200</td> <td style="padding: 5px;">Q</td> <td style="padding: 5px;">45</td> <td style="padding: 5px;">C</td> <td style="padding: 5px;">F</td> </tr> <tr> <td style="text-align: center;">①</td> <td style="text-align: center;">②</td> <td style="text-align: center;">③</td> <td style="text-align: center;">④</td> <td style="text-align: center;">⑤</td> <td style="text-align: center;">⑥</td> </tr> </table>	R	3200	Q	45	C	F	①	②	③	④	⑤	⑥
R	3200	Q	45	C	F								
①	②	③	④	⑤	⑥								
1	- R = Diode												
2	- Essential part number												
3	- Q - Puk												
4	- Voltage code: Code x 100 = V _{RRM} (See Voltage Ratings table)												
5	- C = Ceramic Puk												
6	- F = Fast recovery												